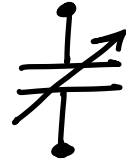




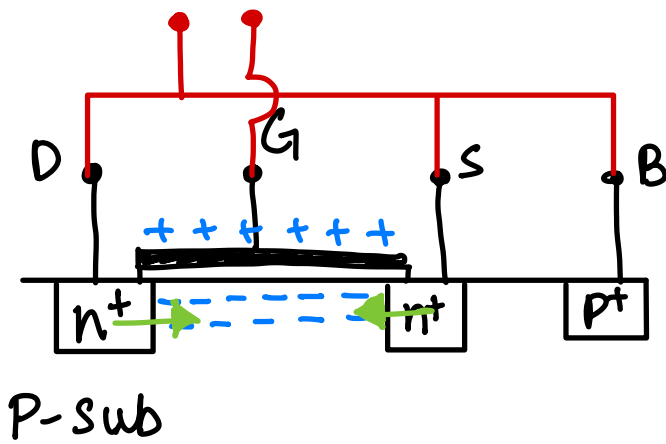
MOS Varactors { Variable Capacitors }

1) Inversion - mode .

2) Accumulation - mode .



NMOS Layout

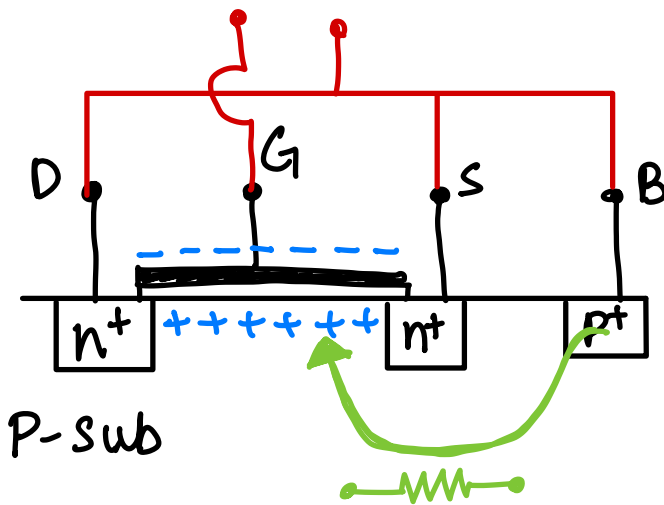


1) Strong inversion

> $V_{GS} \gg V_{th}$.

> $C_{ap} \approx C_{ox}$

> $n^+ \leftrightarrow \text{channel} \leftrightarrow n^+$
form a low resistance bottom plate.

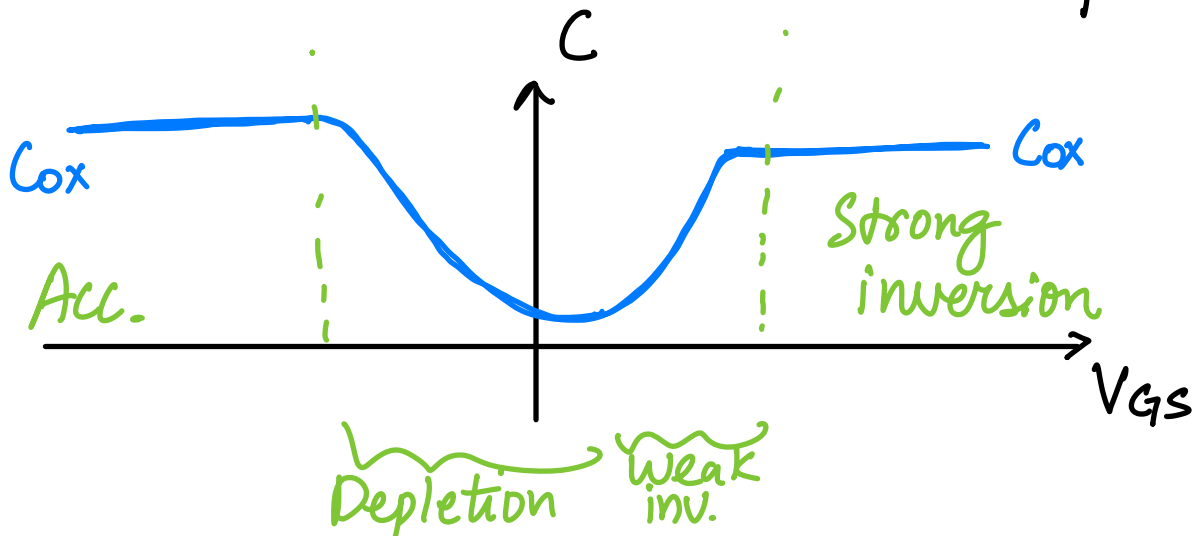


2) Accumulation

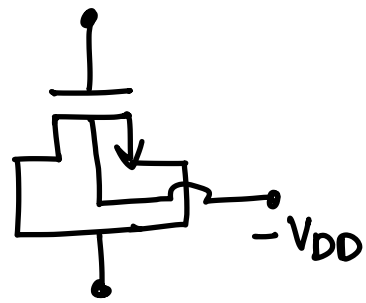
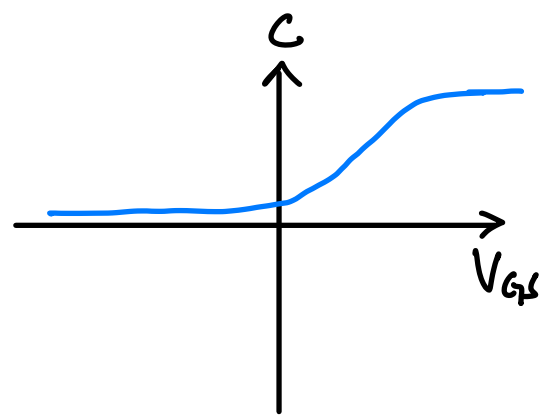
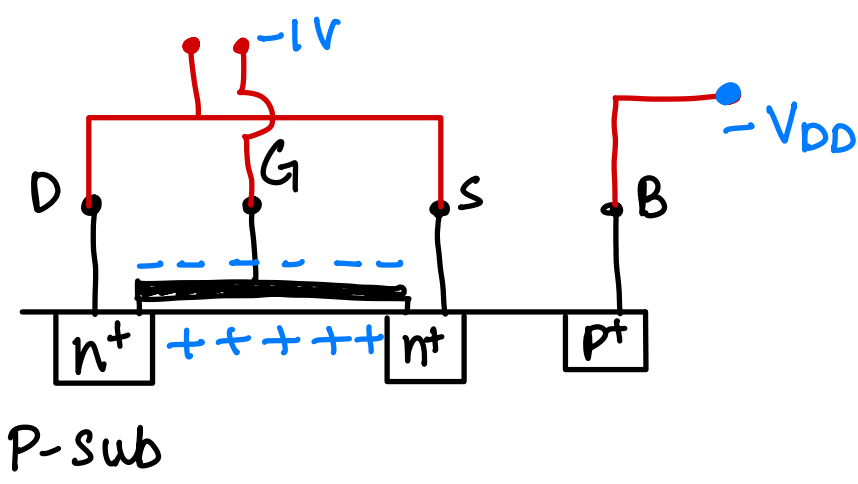
> $V_{GS} < 0$

> $C_{ap} \approx C_{ox}$

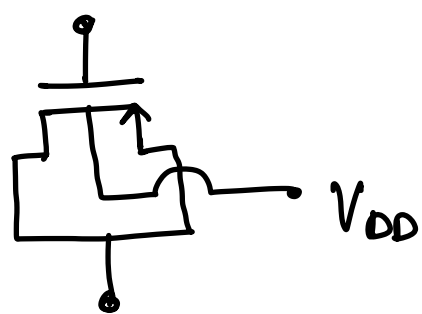
> Large series parasitic res.



I Inversion-mode MOSCAP *(Eliminate accumulation)*

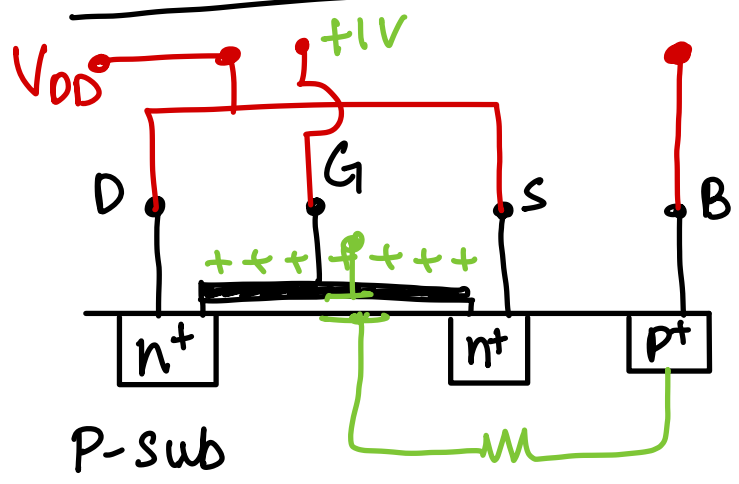


IM-NMOS

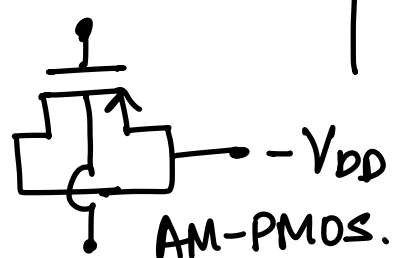
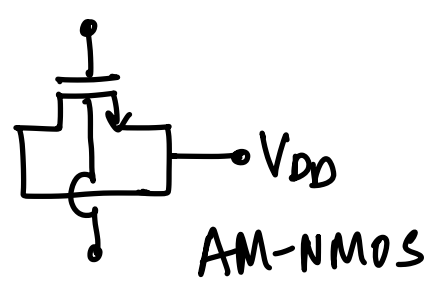
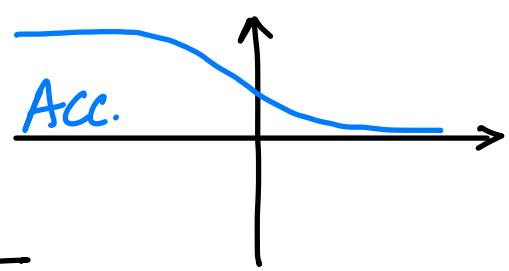


IM-PMOS

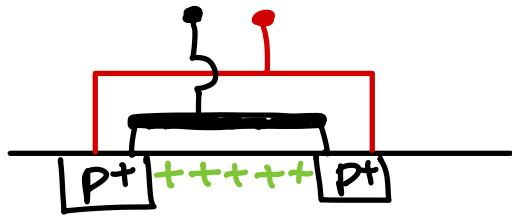
II Accumulation mode MOSCAP *(Eliminate inversion)*



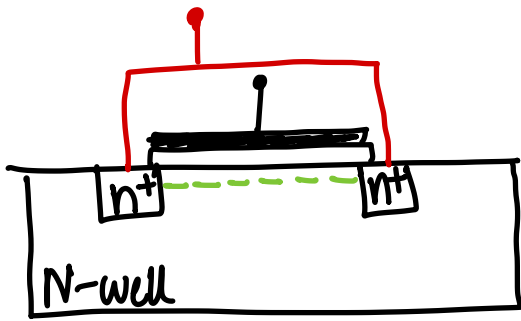
> Be careful about swing & junction breakdown!



Improve accumulation mode MOS caps



P-sub



Psub

- > No par. resistance.
- > No weak inversion.
- > Large supply of maj. carriers nearby.
- > No unnecessary parasitics!
- > Custom Layout & characterization if not available in PDK.